



DRDNB21D

COMPLEX ARRAY FOR DUAL RELAY DRIVER

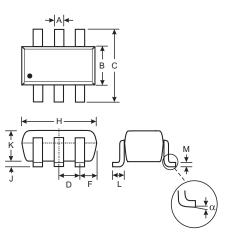
Features

- Epitaxial Planar Die Construction
- Two Pre-Biased Transistors and Two Switching Diodes, Internally Connected in One Package
- Ideally Suited for Automated Assembly Processes
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 standards for High Reliability

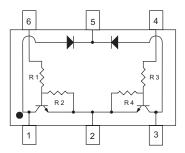
Mechanical Data

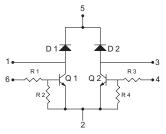
- Case: SOT-363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Last Page
- Ordering Information: See Last Page
- Weight: 0.006 grams (approximate)

R1 = R3 = $2.2k\Omega$ (nominal) R2 = R4 = $47k\Omega$ (nominal)



	SOT-363				
Dim	Min	Max			
Α	0.10	0.30			
В	1.15	1.35			
С	2.00	2.20			
D	0.65 N	ominal			
F	0.30	0.40			
Н	1.80	2.20			
J	— 0.10				
K	0.90	1.00			
L	0.25	0.40			
М	0.10	0.25			
α	0°	8°			
All Din	nensions	in mm			





Maximum Ratings, Total Device @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P _d	200	mW
Thermal Resistance, Junction to Ambient Air (Note 3)	$R_{ heta JA}$	625	°C/W
Operating and Storage Junction Temperature Range	T _j , T _{STG}	-55 to +150	°C

Maximum Ratings, Pre-Biased NPN Transistor @ TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CC}	50	V
Collector-Emitter Voltage	V _{in}	-5 to +12	V
Emitter-Base Voltage	Io	100	mA
Output Current - Continuous (Note 3)	Ic	200	mA

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 3. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



Maximum Ratings, Switching Diode @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V _{RM}	100	V
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	75	V
RMS Reverse Voltage	V _{R(RMS)}	53	V
Forward Continuous Current (Note 3)	I _{FM}	500	mA
Average Rectified Output Current (Note 3)	Io	250	mA
Non-Repetitive Peak Forward Surge Current @ $t = 1.0 \mu s$ @ $t = 1.0 s$	I _{FSM}	4.0 2.0	А

Electrical Characteristics, Pre-Biased NPN Transistor @ TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Innut Voltage	$V_{I(off)}$	0.5	_	$-$ V $V_{CC} = 5V, I_O =$		$V_{CC} = 5V$, $I_{O} = 100 \mu A$
Input Voltage	$V_{I(on)}$	_	_	1.1	V	$V_O = 0.3V, I_O = 5mA$
Output Voltage	V _{O(on)}	_	_	0.3	V	$I_0/I_1 = 50 \text{mA}/0.25 \text{mA}$
Input Current	l _l	_	_	3.6	mA	$V_I = 5V$
Output Current	I _{O(off)}	_	_	0.5	uA	$V_{CC} = 50V$, $V_I = 0V$
DC Current Gain	Gı	80	_	_	_	$V_O = 5V, I_O = 10mA$
Input Resistor Tolerance	ΔR1	-30	_	+30	%	
Resistance Ratio Tolerance	∆R2/R1	-20	_	+20	%	
Gain-Bandwidth Product*	f⊤	_	250	_	MHz	$V_{CE} = 10V$, $I_E = 5mA$, $f = 100MHz$

Transistor - For Reference Only

Electrical Characteristics, Switching Diode @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 4)	V _{(BR)R}	75	_	V	$I_R = 10 \mu A$
Forward Voltage (Note 4)	V _F	0.62 — — —	0.72 0.855 1.0 1.25	V	I _F = 5.0mA I _F = 10mA I _F = 100mA I _F = 150mA
Reverse Current (Note 4)	I _R	_	2.5 50 30 25	μΑ μΑ μΑ nA	$V_R = 75V$ $V_R = 75V$, $T_j = 150^{\circ}C$ $V_R = 25V$, $T_j = 150^{\circ}C$ $V_R = 20V$
Total Capacitance	Ст	_	4.0	pF	V _R = 0, f = 1.0MHz
Reverse Recovery Time	t _{rr}	_	4.0	ns	$I_F = I_R = 10 \text{mA},$ $I_{rr} = 0.1 \text{ x } I_R, R_L = 100 \Omega$

Notes:

- 3. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 4. Short duration pulse test used to minimize self-heating effect.



Device Characteristics

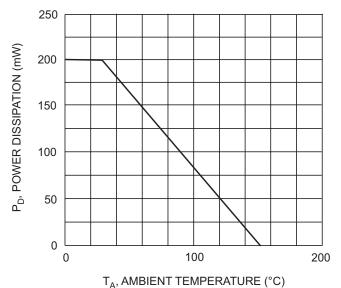
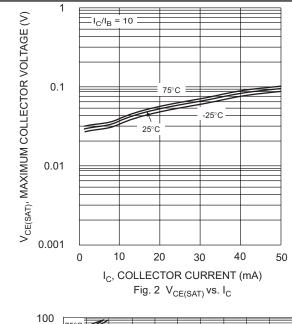
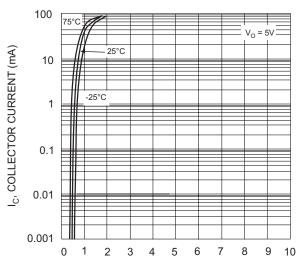


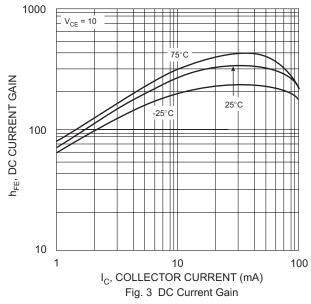
Fig. 1, Power Derating Curve (Total Device)

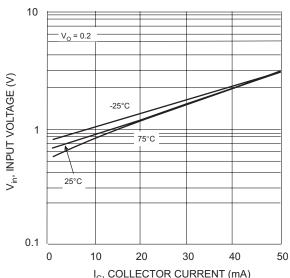
Pre-Biased NPN Transistor Elements





 $\label{eq:Vin} V_{\text{in}}, \text{INPUT VOLTAGE (V)} \\ \text{Fig. 4 Collector Current vs. Input Voltage} \\ \text{DS30756 Rev. 3 - 2}$





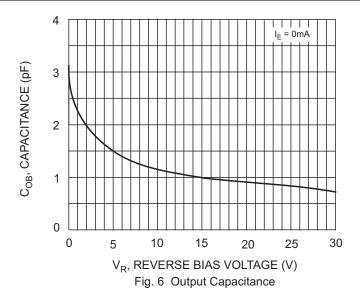
I_C, COLLECTOR CURRENT (mA)
Fig. 5 Input Voltage vs. Collector Current

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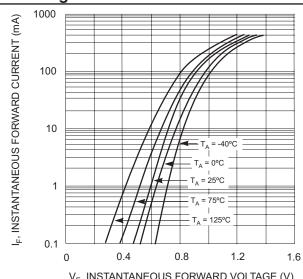
DRDNB21D



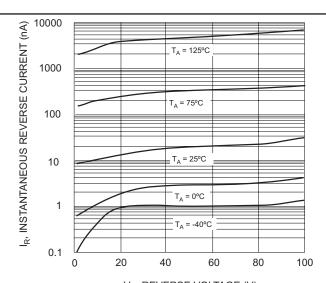
Pre-Biased NPN Transistor Elements (Continued)



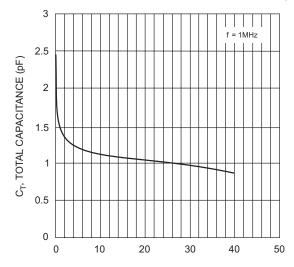
Switching Diode Elements



V_F, INSTANTANEOUS FORWARD VOLTAGE (V) Fig. 7 Typical Forward Characteristics



 V_R , REVERSE VOLTAGE (V) Fig. 8 Typical Reverse Characteristics

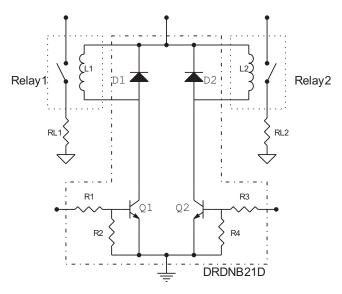


 $\label{eq:VR} {\rm V_{R},\,REVERSE\,\,VOLTAGE\,\,(V)}$ Fig. 9 Typical Capacitance vs. Reverse Voltage

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Typical Application Circuit



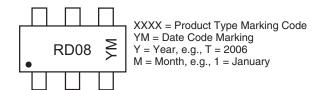
Typical Application Circuit using DRDNB21D with two independent relays.

Ordering Information (Note 5)

Device	Marking Code	Packaging	Shipping		
DRDNB21D-7	RD08	SOT-363	3000/Tape & Reel		

Notes: 5. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



Date Code Key

Year					2005	200	6	2007	2008		2009	
	Code			S	T U		V		W			
Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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